

**SPECIFICATION AMENDMENTS:**

Please amend the specification as follows:

Page 11, lines 6-13, please amend the current paragraph as follows:

The LED epitaxial film 110 is not limited to thicknesses or materials given above. Other inorganic compound materials, such as an aluminum-gallium indium phosphide ( $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ , where  $0 \leq x \leq 1$  and  $0 \leq y \leq 1$ ), a gallium nitride (GaN), an aluminum gallium nitride (AlGaN), and an indium gallium nitride (InGaN), may also be employed. Other than a double hetero-epitaxial structure described in FIG. 4, a single hetero-epitaxial structure and a homo-epitaxial structure can be also applied in LEDs.